

1 46890/DMC/V165

LOW TEMPERATURE ALUMINUM PLANARIZATION PROCESS

5 ABSTRACT OF THE DISCLOSURE

A low temperature aluminum planarization process. Vias, including high aspect ratio vias, are filled using a liner layer, a seed layer, and a fill layer. The device associated with the via is exposed to a reactive gas prior to applying the fill layer
10 to the device.

DMC/AGI/rmw

15
20
25
30
35